

In the Specification:

In the paragraph beginning at line 15 on page 1 and ending at line 17 on page 1, please delete the phrase “<atty. Docket no.: M-7524 US>” at line 16 on page 1 and replace with --US Patent Application No. 09/927,133-- and delete the phrase “even date herewith” at line 17 on page 1 and replace with --August 10, 2001--.

In the paragraph beginning at line 18 on page 1 and ending at line 20 on page 1, please delete the phrase “<atty. Docket no.: M-7526 US>” at line 19 on page 1 and replace with --US Patent Application No. 09/927,988-- and delete the phrase “even date herewith” at line 20 on page 1 and replace with --August 10, 2001--.

The clean versions of the amended paragraphs referred to above appear below:

Clean version of amended paragraph replacing the paragraph beginning at line 15 on page 1 and ending at line 17 on page 1:

1. United States patent application entitled, “Process for Treating ONO Dielectric Film of a Floating Gate Memory Cell”, US Patent Application No. 09/927,133 naming Robert B. Ogle, Jr. and Arvind Halliyal as inventors and filed on August 10, 2001; and

**Clean version of amended paragraph replacing the paragraph beginning at line 18
on page 1 and ending at line 20 on page 1:**

2. United States patent application entitled, "Process for Treating ONO Dielectric Film of a Floating Gate Memory Cell", US Patent Application No. 09/927,988 naming Robert B. Ogle, Jr. and Arvind Halliyal as inventors and filed on August 10, 2001.